

N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I _D (A)	Q _g (Typ.)				
20	0.300 at $V_{GS} = 4.5 \text{ V}$	0.9	3.5				
	0.350 at V _{GS} = 2.5 V	0.7	3.5				

FEATURES

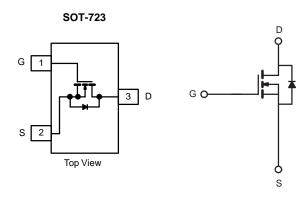
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- · Load Switching for Portable Devices
- DC/DC Converter



ABSOLUTE MAXIMUM RATINGS	$(T_A = 25 ^{\circ}C, unlet)$	ess otherwise	noted)		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V_{GS}	± 12		V
0 " D : 0 1/T 15000)3	T _A = 25 °C	- I _D	0.9	0.72	•
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		0.68	0.57	
Pulsed Drain Current (t = 300 μs) ^b		I _{DM}	3.5		Α
Continuous Source Current (Diode Conduction) ^a		I _S	0.72	0.6	
D D: : :: 3	T _A = 25 °C	В	0.35	0.28	10/
Power Dissipation ^a	T _A = 70 °C	P _D	0.21	0.16	W
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marrian Incation to Ambient	t ≤ 5 s	R _{thJA}	120	145		
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	140	175	°C/W	
Maximum Junction-to-Foot	Steady State	R _{thJF}	62	78		

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.

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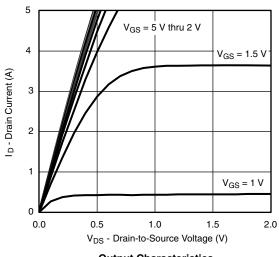
			Limits					
Parameter	Symbol	Test Conditions	Min.	Тур. Мах.		Unit		
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V		
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.50		0.90	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA		
Zava Cata Valtaga Dvain Cuvvant	1	V _{DS} = 20 V, V _{GS} = 0 V			1			
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			75	μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 4.5 \text{ V}$	6			Α		
	D	$V_{GS} = 4.5 \text{ V}, I_D = 0.9 \text{A}$		0.300		0		
Drain-Source On-Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 0.7 \text{ A}$		0.350		Ω		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_D = 0.9 \text{ A}$		13		S		
Diode Forward Voltage	V_{SD}	I _S = 0.95 A, V _{GS} = 0 V		0.7	1.2	V		
Dynamic ^b				•				
Total Gate Charge	Q_g			1.5	1.9			
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 0.9 \text{A}$		0.25		nC		
Gate-Drain Charge	Q_{gd}			0.40				
Gate Resistance	R_{g}	f = 1 MHz	2	4	8	Ω		
Switching			<u>'</u>	<u>'</u>				
Turn-On Delay Time	t _{d(on)}			8	15			
Rise Time	t _r	V_{DD} = 10 V, R_L = 2.78 Ω		7	15			
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 0.9$ A, $V_{GEN}=4.5$ V, $R_g=1$ Ω		30	45	ns		
Fall Time	t _f			7	15			
Source-Drain Reverse Recovery Time	t _{rr}	L = 0.0 A dl/dt = 100 A/up		8.5	15			
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = 0.9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		2	4	nC		

Notes:

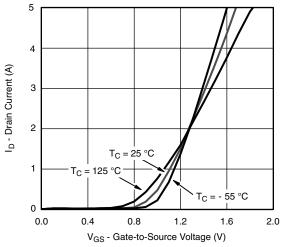
- a. Pulse test: Pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



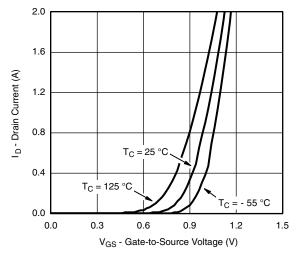
Output Characteristics

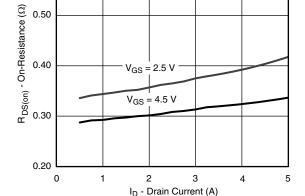


Transfer Characteristics



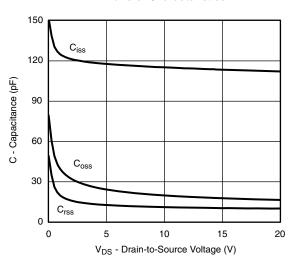
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



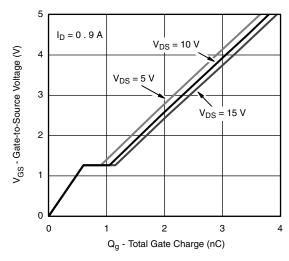


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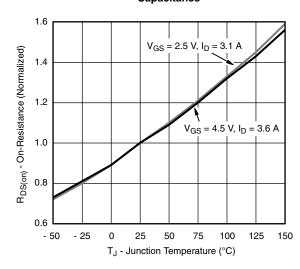
Transfer Characteristics



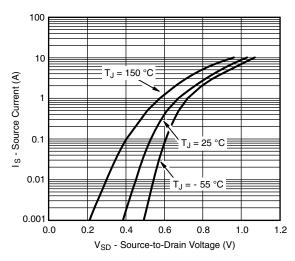
On-Resistance vs. Drain Current



Capacitance



Gate Charge

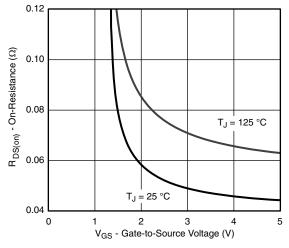


On-Resistance vs. Junction Temperature

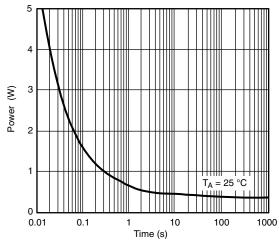
Source-Drain Diode Forward Voltage



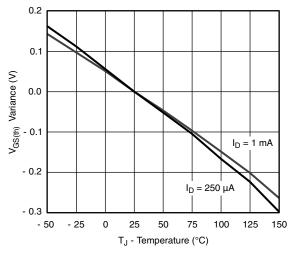
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



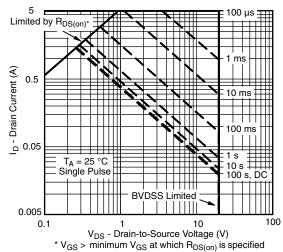
On-Resistance vs. Gate-to-Source Voltage



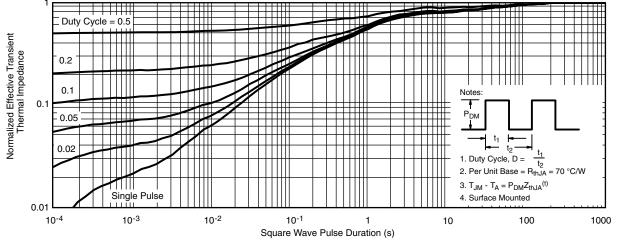
Single Pulse Power



Threshold Voltage



Safe Operating Area, Junction-to-Ambient

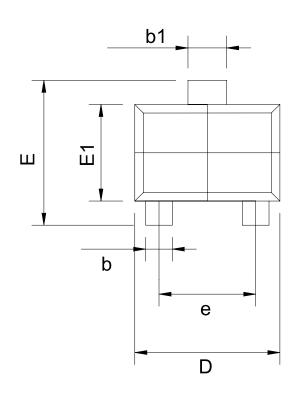


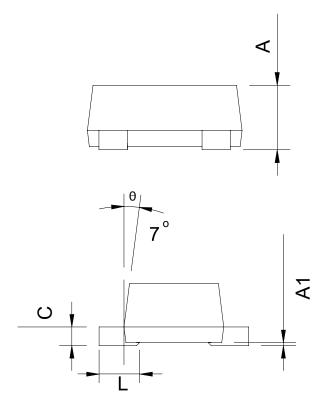
Normalized Thermal Transient Impedance, Junction-to-Ambient

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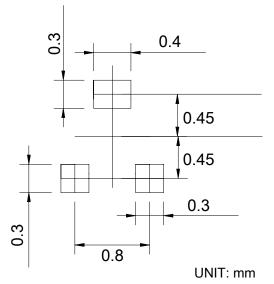
SOT-723: 3 Leads





Ş	SOT-723					
SYMBOL	MILLIM	ETERS	INCHES			
<u>P</u>	MIN.	MAX.	MIN.	MAX.		
Α	-	0.500	-	0.020		
A1	0.000	0.050	0.000	0.002		
b	0.170	0.270	0.007	0.011		
b1	0.270	0.370	0.011	0.015		
С	-	0.150	-	0.006		
D	1.150	1.250	0.045	0.049		
Е	1.150	1.250	0.045	0.049		
E1	0.750	0.850	0.030	0.033		
е	0.800	TYP.	0.03	1 TYP.		
L	0.32 BSC		0.013	13 BSC		
-	°F	REF.	°F	REF.		

RECOMMENDED LAND PATTERN



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